

■ IEEE EDS Kansai Chapter IMFEDK Best Paper Award

Paper ID: B-2
Titled: *"Influence of Edge Roughness on the Performance of Graphene Nano-Ribbon Devices"*
Authors: **Satofumi Souma**¹, M. Ogawa¹, T. Yamamoto², K. Watanabe³
Affiliation: ¹Kobe University, ²The University of Tokyo, ³Tokyo University of Science

■ IEEE EDS Kansai Chapter IMFEDK Student Paper Award

Author: **Hiroki Miyake**, Paper ID: SA-1
Titled: *"Demonstration of Common-Emitter Mode Operation in AlGaIn/SiC Heterojunction Bipolar Transistors"*
Coauthors: T. Kimoto, J. Suda, Affiliation: Kyoto University

Author: **Eri Ogawa**, Paper ID: SA-4
Titled: *"Effects of High-Temperature Anneal on Surface Properties of Mg-Doped GaN"*
Coauthor: T. Hashizume, Affiliation: Hokkaido University

Author: **Keita Yoshikawa**, Paper ID: SB-9
Titled: *"Multi-Axis Force Detection Using Piezoelectric Resonant Cantilever Sensors"*
Coauthors: T. Kawata, K. Yamashita, M. Noda Affiliation: Kyoto Institute of Technology

Author: **Hironori Yoshioka**, Paper ID: SB-11
Titled: *"One-Dimensional Quantum Confinement Effects in Si-Nanowire MOSFETs"*
Coauthors: N. Morioka, J. Suda, T. Kimoto Affiliation: Kyoto University

Author: **Kosuke Ohara**¹, Paper ID: SC-2
Titled: *"Floating Gate Memory Devices Based on Ferritin Nanodots on High-k Gate Dielectrics"*
Coauthors: Y. Uraoka¹, T. Fuyuki¹, I. Yamashita¹,
T. Yaegashi², M. Moniwa², M. Yoshimaru²
Affiliation: ¹Nara Institute of Science and Technology,
²Semiconductor Technology Academic Research Center

Author: **Shunsuke Nakano**¹, Paper ID: SC-3
Titled: *"Gate, Source and Drain Engineering for sub-100-nm-Channel Si-Wire Gate-All-Around MOSFET"*
Coauthors: O. Hayashi¹, Y. Omura¹, S. Yamakawa², H. Wakabayashi²
Affiliation: ¹Kansai University, ²Sony Corp.